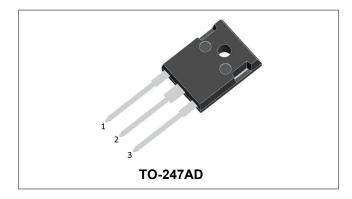






30CPQ050/30CPQ060 SCHOTTKY RECTIFIER



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ \end{array}$	-	50(30CPQ050) 60(30CPQ060)	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=112°C, rectangular wave form	15(Per Leg) 30(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse, T _C = 25 °C	315	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (Per Leg)*	V _{F1}	@ 15A, Pulse, T _J = 25 °C @ 30A, Pulse, T _J = 25 °C	0.55 0.61	0.60 0.80	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C @ 30A, Pulse, T _J = 125 °C	0.47 0.58	0.56 0.70	V
Reverse Current (Per Leg)*	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25 ^{\circ}\text{C}$	0.2	0.8	mA
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 125 ^{\circ}\text{C}$	70	100	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	650	720	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 μ s, duty cycle < 2%

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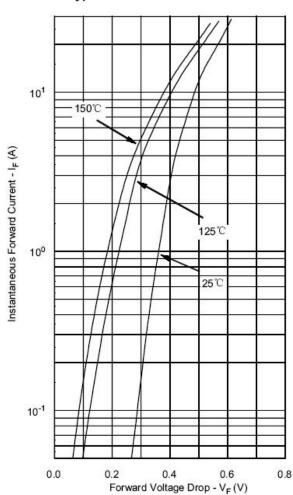


Thermal-Mechanical Specifications:

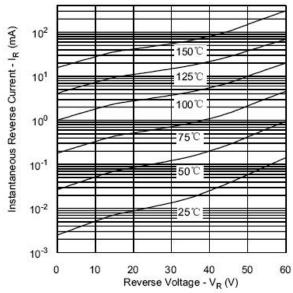
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	2.2(Peg Leg) 1.10(Peg Device)	°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.24	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

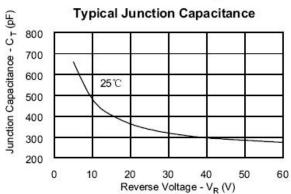
Ratings and Characteristics Curves

Typical Forward Characteristics



Typical Reverse Characteristics





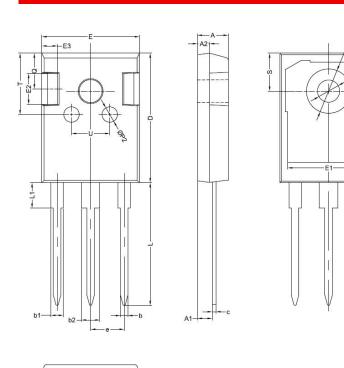
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Mechanical Dimensions TO-247AD



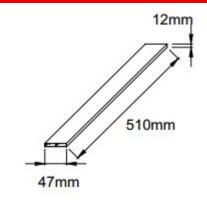
CVMDOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.40		
b1	1.80	2.00	2.20		
b2	2.80	3.00	3.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.55			
D2 E		1.20			
Е	15.45	15.80	16.00		
E1		13.30			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.70		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1		7.40		
P2		2.50			
Q		5.80			
Q S T	6.05	6.15	6.25		
		10.00			
U		6.20			

Ordering Information:

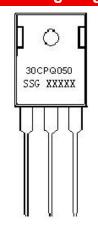
Device	Package	Shipping	
30CPQ050(060)	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

= Forward Current (30A) 30 = Configuration С = Device Type = Reverse Voltage (50V) PQ

050 SSG = SSG

YY = Year WW = Week = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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